

### Final datasheet

### High speed and low saturation voltage 650 V TRENCHSTOP™ IGBT7 technology copacked with soft, fast recovery Emitter Controlled 7 diode

#### Features

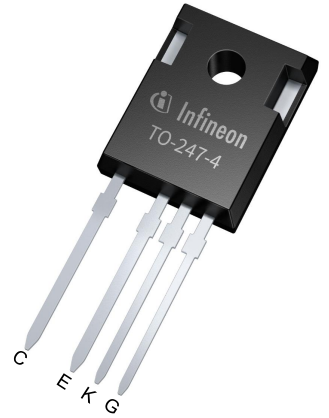
- $V_{CE} = 650\text{ V}$
- $I_C = 75\text{ A}$
- Low switching losses
- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Very soft, fast recovery antiparallel diode
- Smooth switching behavior
- Humidity robustness
- Optimized for hard switching, two- and three-level topologies
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

#### Potential applications

- Industrial UPS
- EV-Charging
- String inverter
- Welding

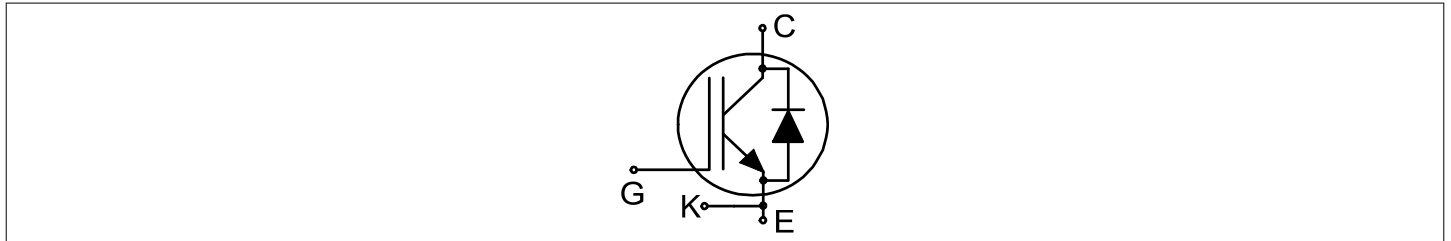
#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



- Lead-free
- Green
- Halogen-free
- RoHS

#### Description



Type	Package	Marking
IKZA75N65EH7	PG-TO247-4-STD-NT3.7	K75EEH7

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## 1 Package

**Table 1 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	$L_E$			13		nH
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	$M$	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.34	0.44	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.45	0.58	K/W

## 2 IGBT

**Table 2 Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	$V_{CE}$	$T_{vj} \geq 25 \text{ °C}$	650	V	
DC collector current, limited by $T_{vjmax}$	$I_C$	limited by bondwire	$T_c = 25 \text{ °C}$	80	A
			$T_c = 100 \text{ °C}$	80	
Pulsed collector current, $t_p$ limited by $T_{vjmax}$	$I_{Cpulse}$		300	A	
Turn-off safe operating area		$V_{CE} \leq 650 \text{ V}$ , $t_p \leq 1 \text{ }\mu\text{s}$ , $T_{vj} \leq 175 \text{ °C}$	300	A	
Gate-emitter voltage	$V_{GE}$		$\pm 20$	V	
Transient gate-emitter voltage	$V_{GE}$	$t_p \leq 10 \text{ }\mu\text{s}$ , $D < 0.01$	$\pm 30$	V	
Power dissipation	$P_{tot}$		$T_c = 25 \text{ °C}$	338	W
			$T_c = 100 \text{ °C}$	148	

**Table 3 Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.4	1.65	V
			$T_{vj} = 175\text{ °C}$		1.6		
Gate-emitter threshold voltage	$V_{GETh}$	$I_C = 0.66\text{ mA}, V_{CE} = V_{GE}$		2.9	3.85	4.8	V
Zero gate-voltage collector current	$I_{CES}$	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			25	$\mu\text{A}$
			$T_{vj} = 175\text{ °C}$		2600		
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$				100	nA
Transconductance	$g_{fs}$	$I_C = 75\text{ A}, V_{CE} = 20\text{ V}$			116		S
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			3886		pF
Output capacitance	$C_{oes}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			123.7		pF
Reverse transfer capacitance	$C_{res}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$			16.8		pF
Gate charge	$Q_G$	$V_{CC} = 520\text{ V}, I_C = 75\text{ A}, V_{GE} = 15\text{ V}$			152		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C},$ $I_C = 75\text{ A}$		26		ns
			$T_{vj} = 175\text{ °C},$ $I_C = 75\text{ A}$		24		
Rise time (inductive load)	$t_r$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C},$ $I_C = 75\text{ A}$		13		ns
			$T_{vj} = 175\text{ °C},$ $I_C = 75\text{ A}$		16		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C},$ $I_C = 75\text{ A}$		199		ns
			$T_{vj} = 175\text{ °C},$ $I_C = 75\text{ A}$		223		
Fall time (inductive load)	$t_f$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C},$ $I_C = 75\text{ A}$		15		ns
			$T_{vj} = 175\text{ °C},$ $I_C = 75\text{ A}$		19		
Turn-on energy	$E_{on}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ °C},$ $I_C = 75\text{ A}$		0.75		mJ
			$T_{vj} = 175\text{ °C},$ $I_C = 75\text{ A}$		1.4		

**(table continues...)**

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy	$E_{off}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		0.84	mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		1.5	
Total switching energy	$E_{ts}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 10\ \Omega,$ $R_{G(off)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		1.59	mJ
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_C = 75\text{ A}$		2.9	
Operating junction temperature	$T_{vj}$		-40		175	$^\circ\text{C}$

### 3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Diode forward current, limited by $T_{vjmax}$	$I_F$	limited by bondwire	$T_c = 25\text{ }^\circ\text{C}$	80	A
			$T_c = 100\text{ }^\circ\text{C}$	80	
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpulse}$		300	A	
Power dissipation	$P_{tot}$		$T_c = 25\text{ }^\circ\text{C}$	258	W
			$T_c = 100\text{ }^\circ\text{C}$	129	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode forward voltage	$V_F$	$I_F = 75\text{ A}$	$T_{vj} = 25\text{ }^\circ\text{C}$		1.65	V
			$T_{vj} = 175\text{ }^\circ\text{C}$		1.55	
Diode reverse recovery time	$t_{rr}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 75\text{ A}$		56	ns
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 75\text{ A}$		108	
Diode reverse recovery charge	$Q_{rr}$	$V_R = 400\text{ V}, R_{G(on)} = 10\ \Omega$	$T_{vj} = 25\text{ }^\circ\text{C},$ $I_F = 75\text{ A}$		1.87	$\mu\text{C}$
			$T_{vj} = 175\text{ }^\circ\text{C},$ $I_F = 75\text{ A}$		4.5	

(table continues...)

**Table 5 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Diode peak reverse recovery current	$I_{rrm}$	$V_R = 400 \text{ V}, R_{G(on)} = 10 \text{ } \Omega$	$T_{vj} = 25 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		59.4	A
			$T_{vj} = 175 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		86.3	
Diode peak rate of fall of reverse recovery current	$di_{rr}/dt$	$V_R = 400 \text{ V}, R_{G(on)} = 10 \text{ } \Omega$	$T_{vj} = 25 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		-1620	A/ $\mu\text{s}$
			$T_{vj} = 175 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		-1760	
Reverse recovery energy	$E_{rec}$	$V_R = 400 \text{ V}, R_{G(on)} = 10 \text{ } \Omega$	$T_{vj} = 25 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		0.49	mJ
			$T_{vj} = 175 \text{ } ^\circ\text{C},$ $I_F = 75 \text{ A}$		1.17	
Operating junction temperature	$T_{vj}$		-40		175	$^\circ\text{C}$

**Note:** For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

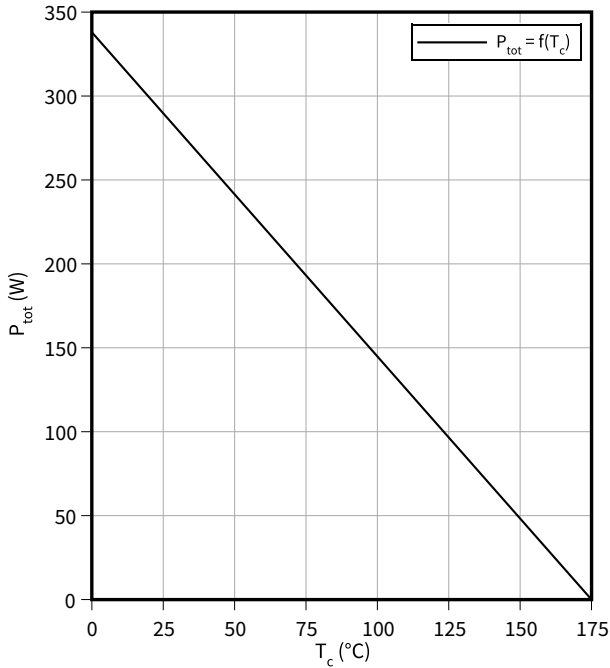
Electrical Characteristic at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified.

Dynamic test circuit, parasitic inductance  $L_\sigma = 8 \text{ nH}$ , parasitic capacitor  $C_\sigma = 30 \text{ pF}$  from Fig. E. Energy losses include "tail" and diode reverse recovery.

## 4 Characteristics diagrams

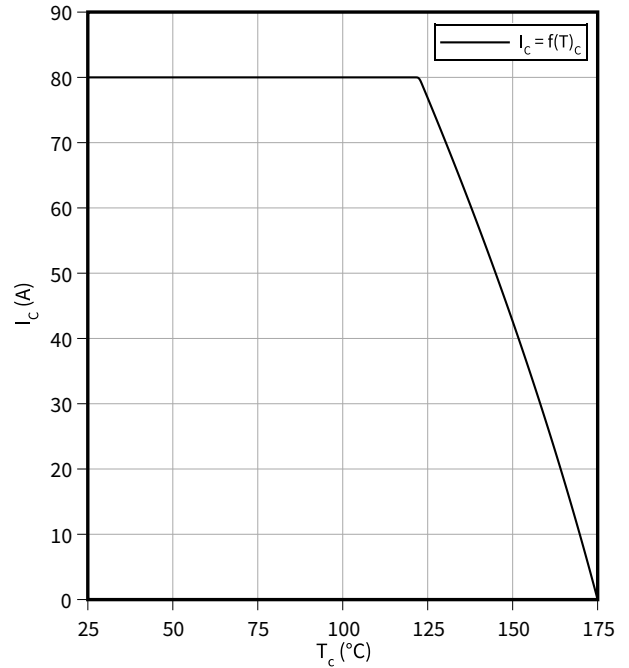
### Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}$



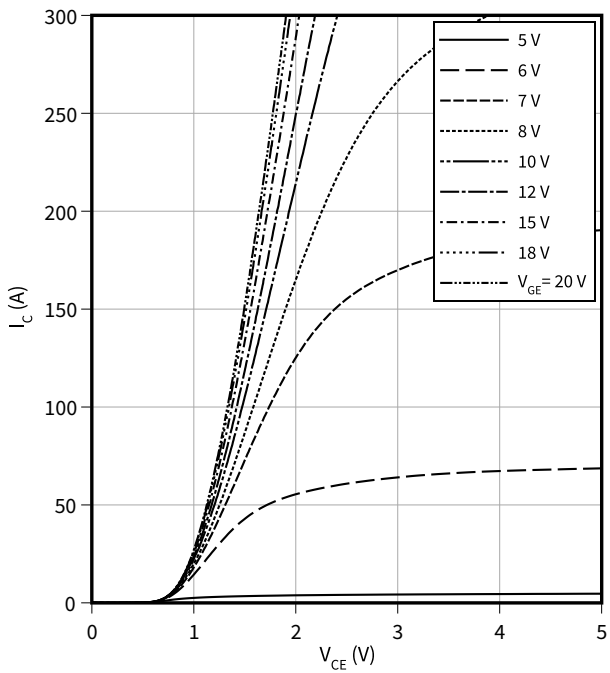
### Collector current as a function of case temperature

$I_C = f(T_c)$   
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



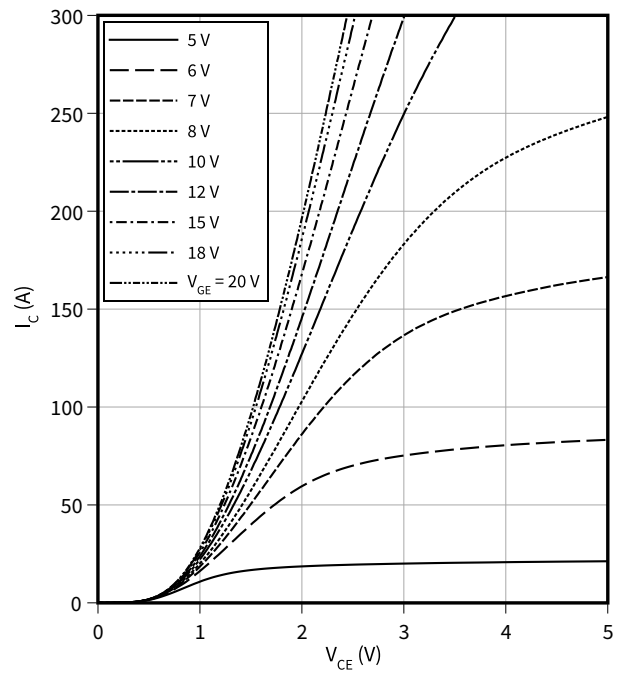
### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 25\text{ °C}$



### Typical output characteristic

$I_C = f(V_{CE})$   
 $T_{vj} = 175\text{ °C}$

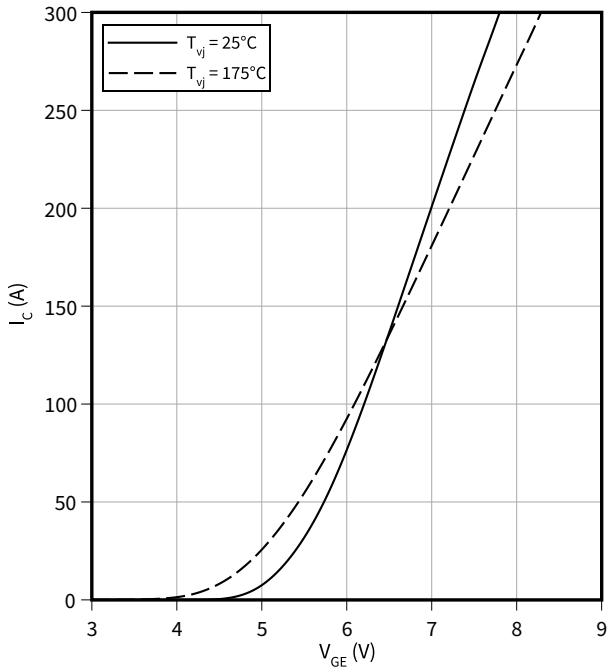


**4 Characteristics diagrams**

**Typical transfer characteristic**

$I_C = f(V_{GE})$

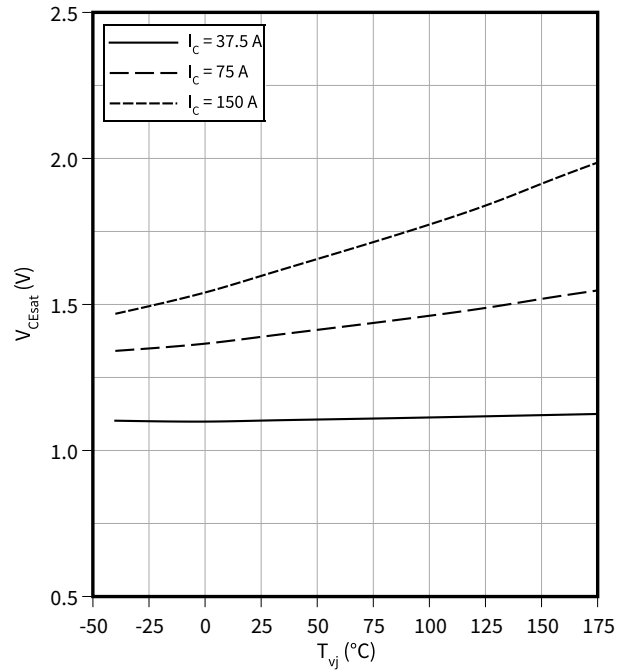
$V_{CE} = 20\text{ V}$



**Typical collector-emitter saturation voltage as a function of junction temperature**

$V_{CEsat} = f(T_{vj})$

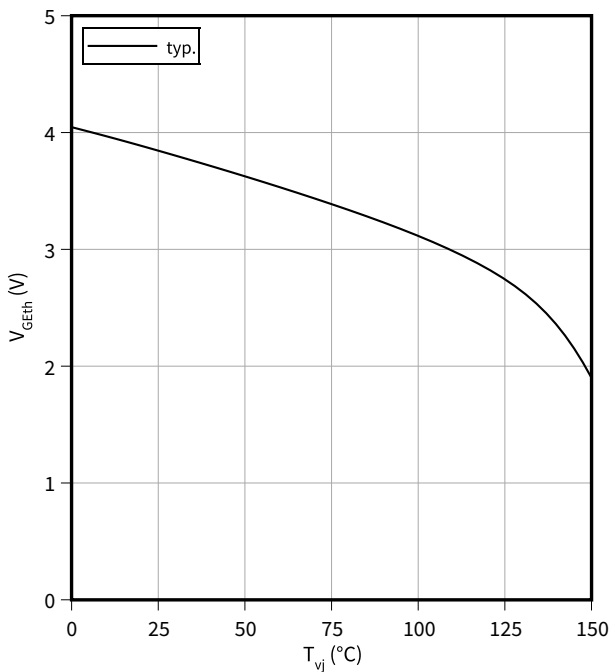
$V_{GE} = 15\text{ V}$



**Gate-emitter threshold voltage as a function of junction temperature**

$V_{GEth} = f(T_{vj})$

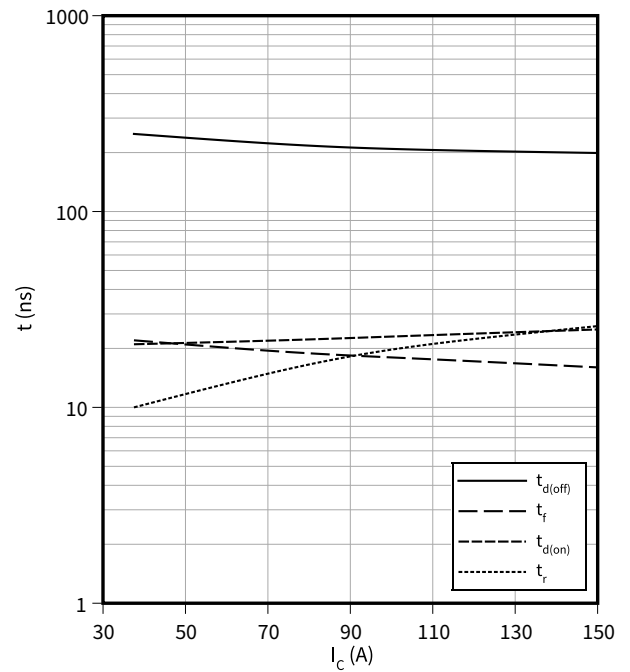
$I_C = 0.66\text{ mA}$



**Typical switching times as a function of collector current**

$t = f(I_C)$

$V_{CC} = 400\text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$



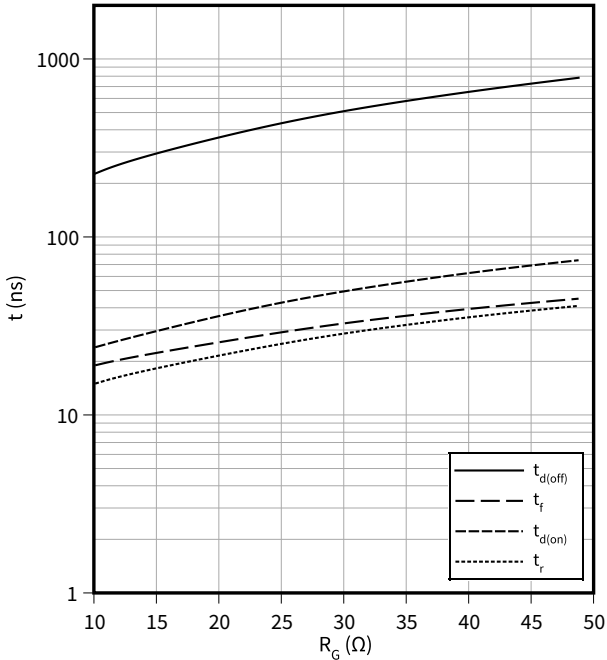


4 Characteristics diagrams

**Typical switching times as a function of gate resistor**

$t = f(R_G)$

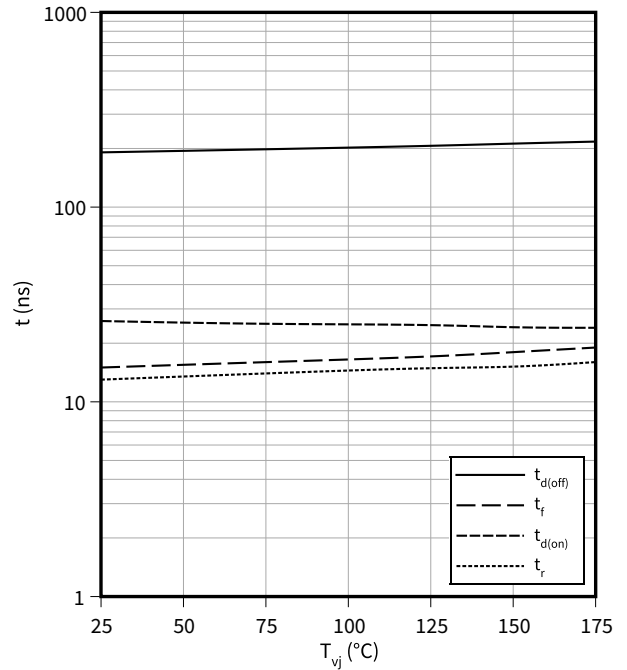
$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$



**Typical switching times as a function of junction temperature**

$t = f(T_{vj})$

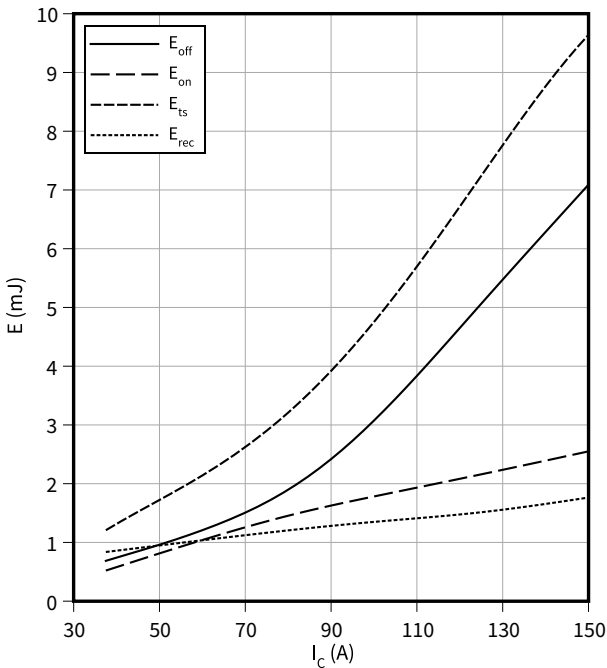
$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$



**Typical switching energy losses as a function of collector current**

$E = f(I_C)$

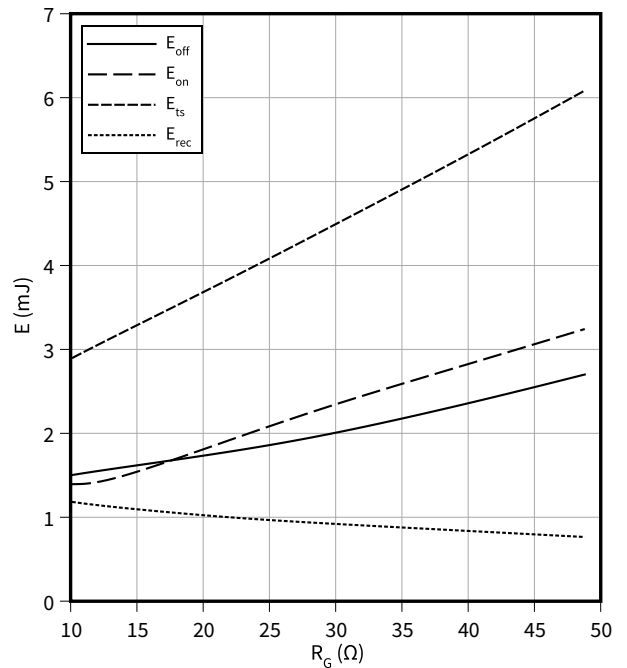
$V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$



**Typical switching energy losses as a function of gate resistor**

$E = f(R_G)$

$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$

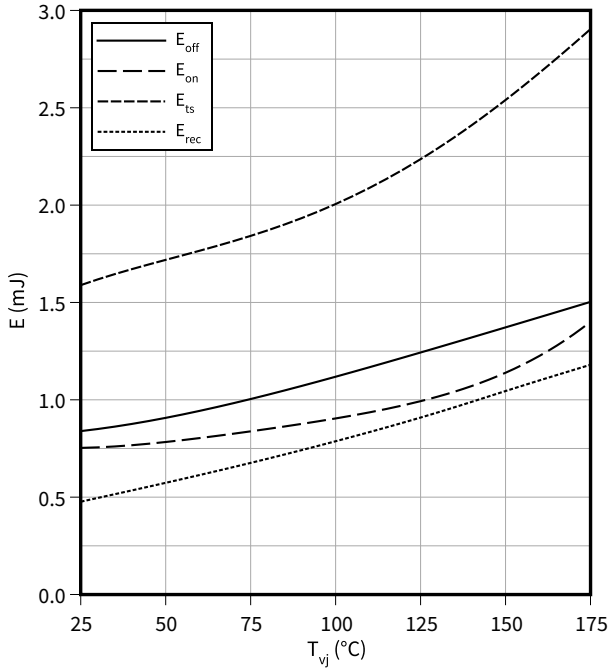


**4 Characteristics diagrams**

**Typical switching energy losses as a function of junction temperature**

$E = f(T_{vj})$

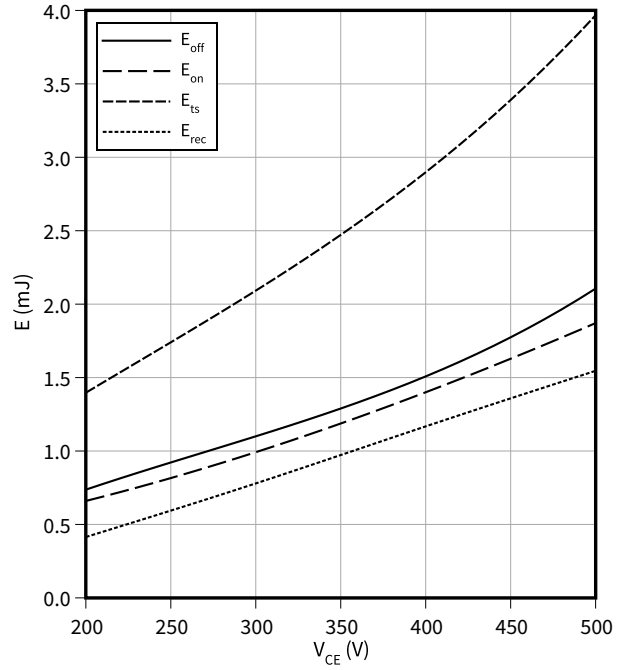
$I_C = 75\text{ A}, V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$



**Typical switching energy losses as a function of collector emitter voltage**

$E = f(V_{CE})$

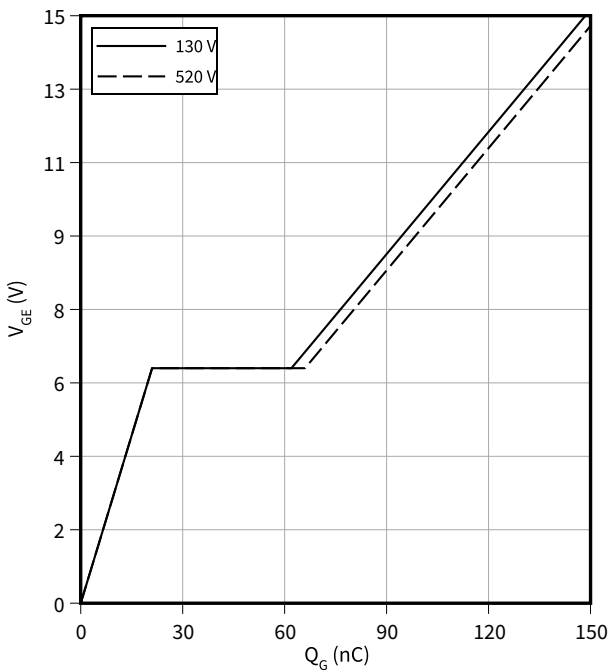
$I_C = 75\text{ A}, T_{vj} = 175\text{ °C}, V_{GE} = 0/15\text{ V}, R_G = 10\ \Omega$



**Typical gate charge**

$V_{GE} = f(Q_G)$

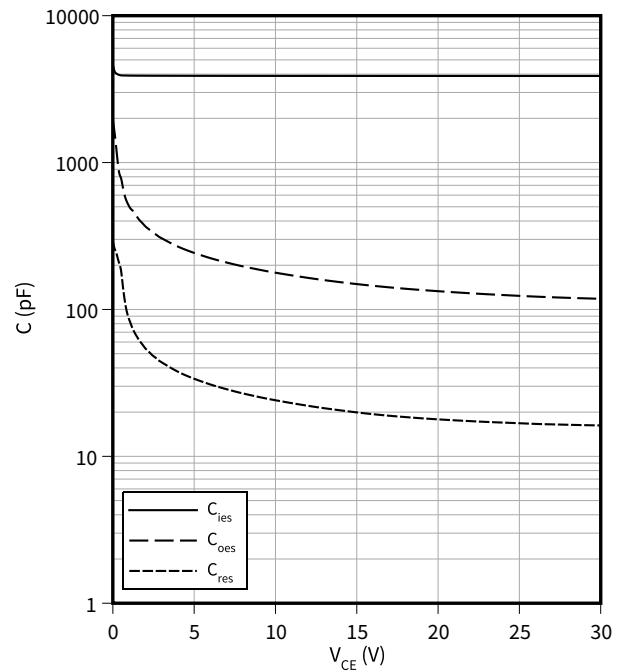
$I_C = 75\text{ A}$



**Typical capacitance as a function of collector-emitter voltage**

$C = f(V_{CE})$

$f = 100\text{ kHz}, V_{GE} = 0\text{ V}$

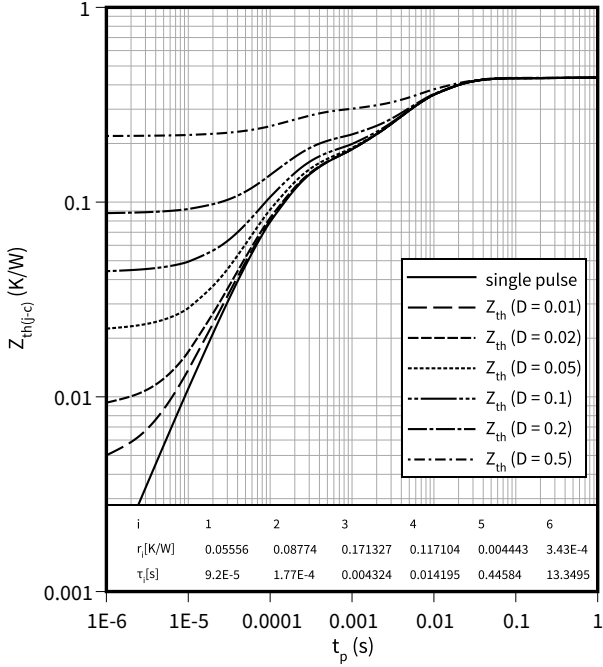


**4 Characteristics diagrams**

**IGBT transient thermal impedance as a function of pulse width**

$Z_{th(j-c)} = f(t_p)$

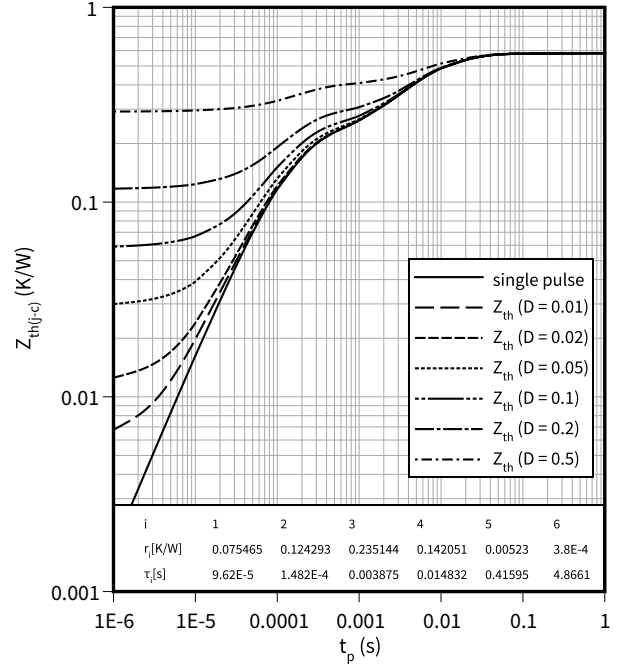
$D = t_p/T$



**Diode transient thermal impedance as a function of pulse width**

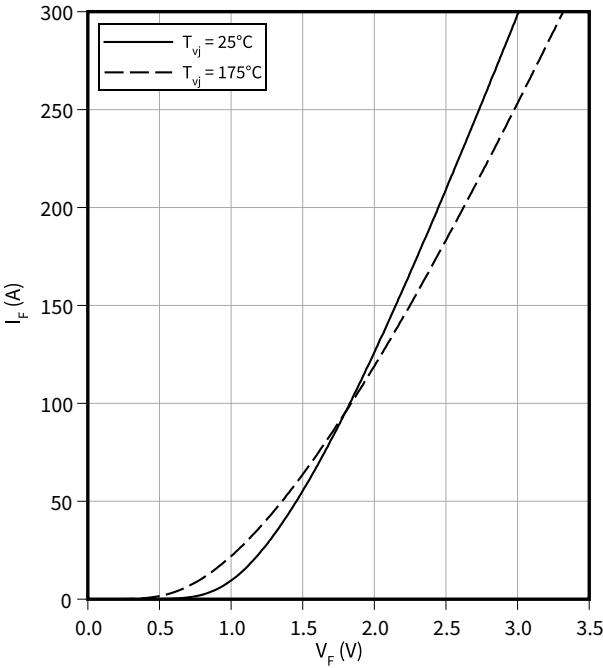
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$



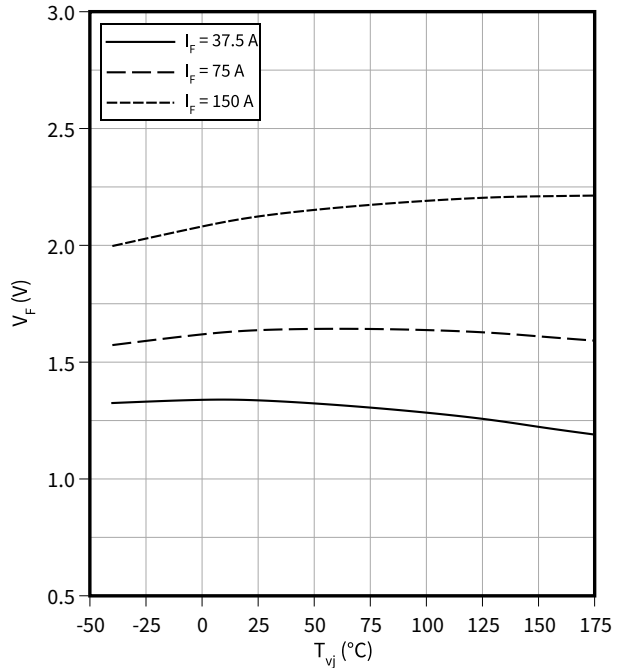
**Typical diode forward current as a function of forward voltage**

$I_F = f(V_F)$



**Typical diode forward voltage as a function of junction temperature**

$V_F = f(T_{vj})$

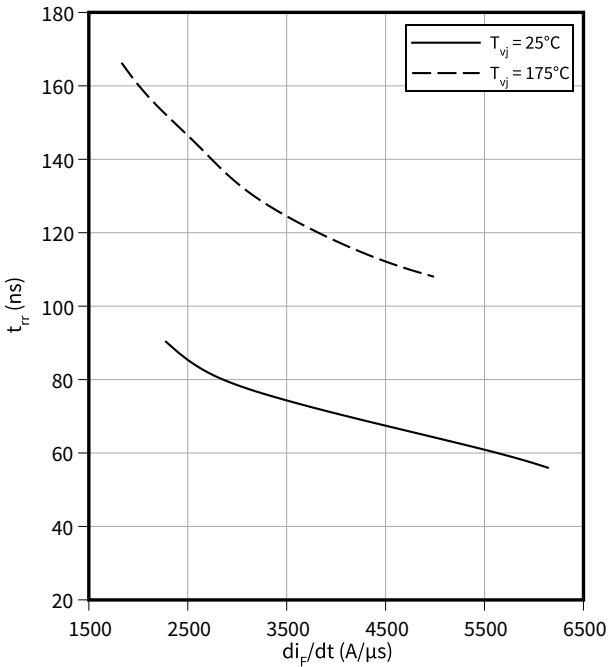


**4 Characteristics diagrams**

**Typical reverse recovery time as a function of diode current slope**

$t_{rr} = f(di_F/dt)$

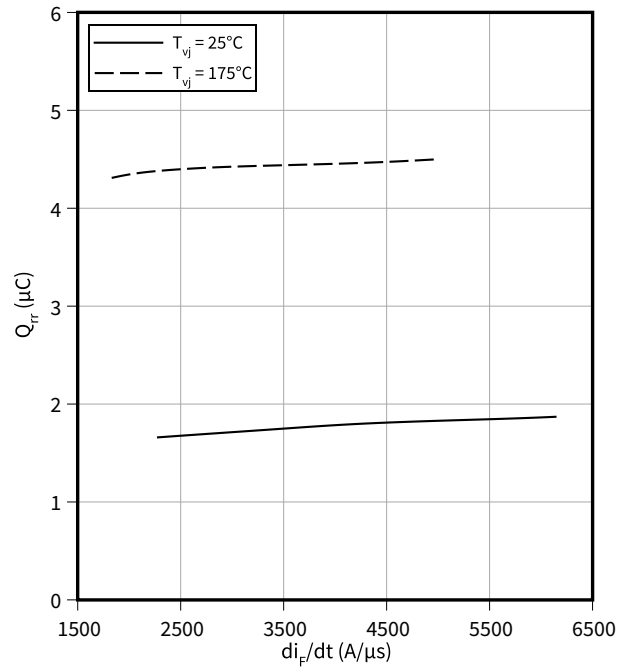
$V_R = 400\text{ V}, I_F = 75\text{ A}$



**Typical reverse recovery charge as a function of diode current slope**

$Q_{rr} = f(di_F/dt)$

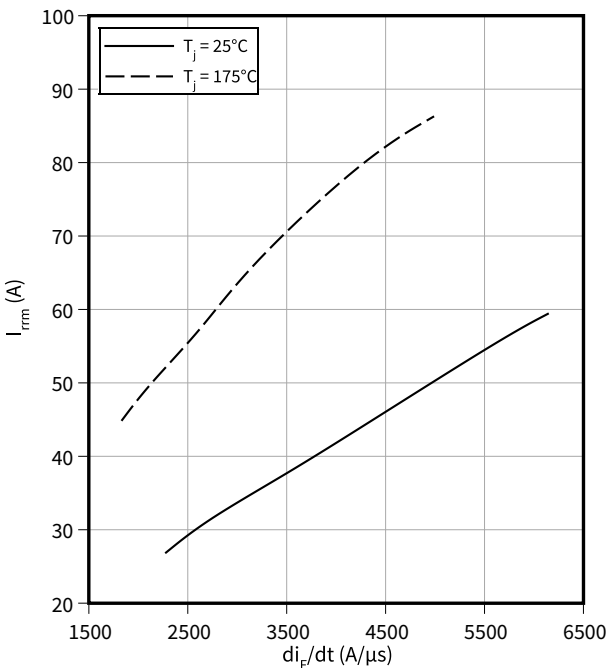
$V_R = 400\text{ V}, I_F = 75\text{ A}$



**Typical reverse recovery current as a function of diode current slope**

$I_{rrm} = f(di_F/dt)$

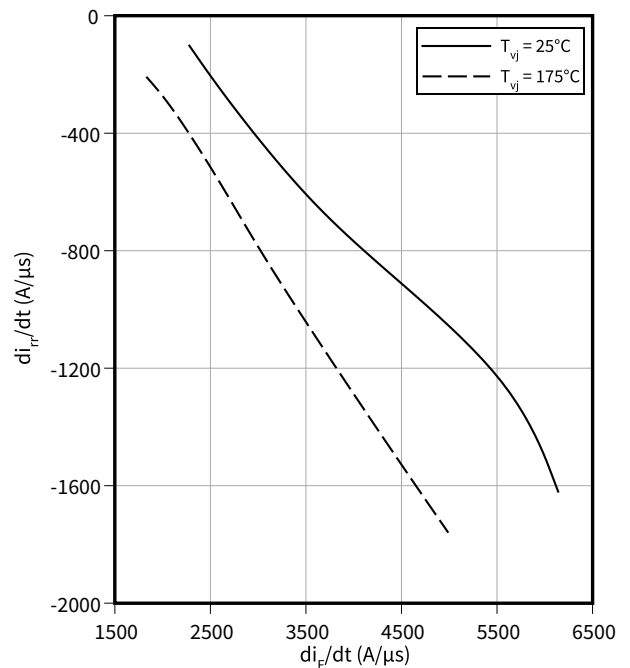
$V_R = 400\text{ V}, I_F = 75\text{ A}$



**Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**

$di_{rr}/dt = f(di_F/dt)$

$V_R = 400\text{ V}, I_F = 75\text{ A}$

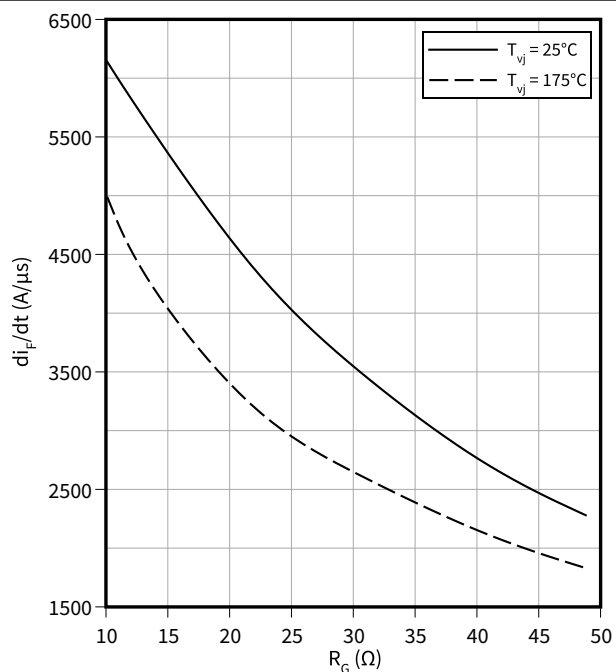


**4 Characteristics diagrams**

**Typical diode current slope as a function of gate resistor**

$di_F/dt = f(R_G)$

$V_R = 400\text{ V}, I_F = 75\text{ A}$



5 Package outlines

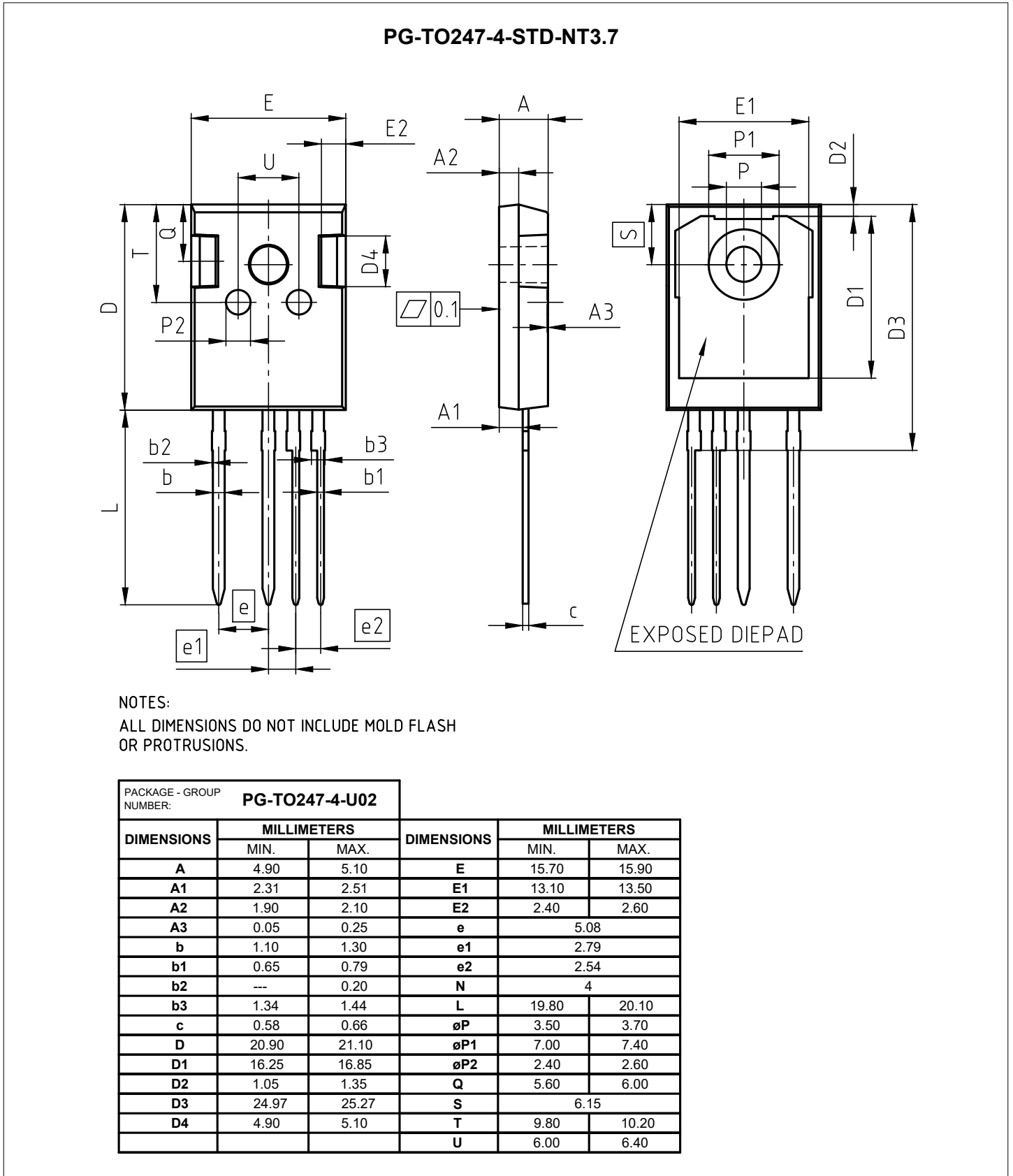


Figure 1

6 Testing conditions

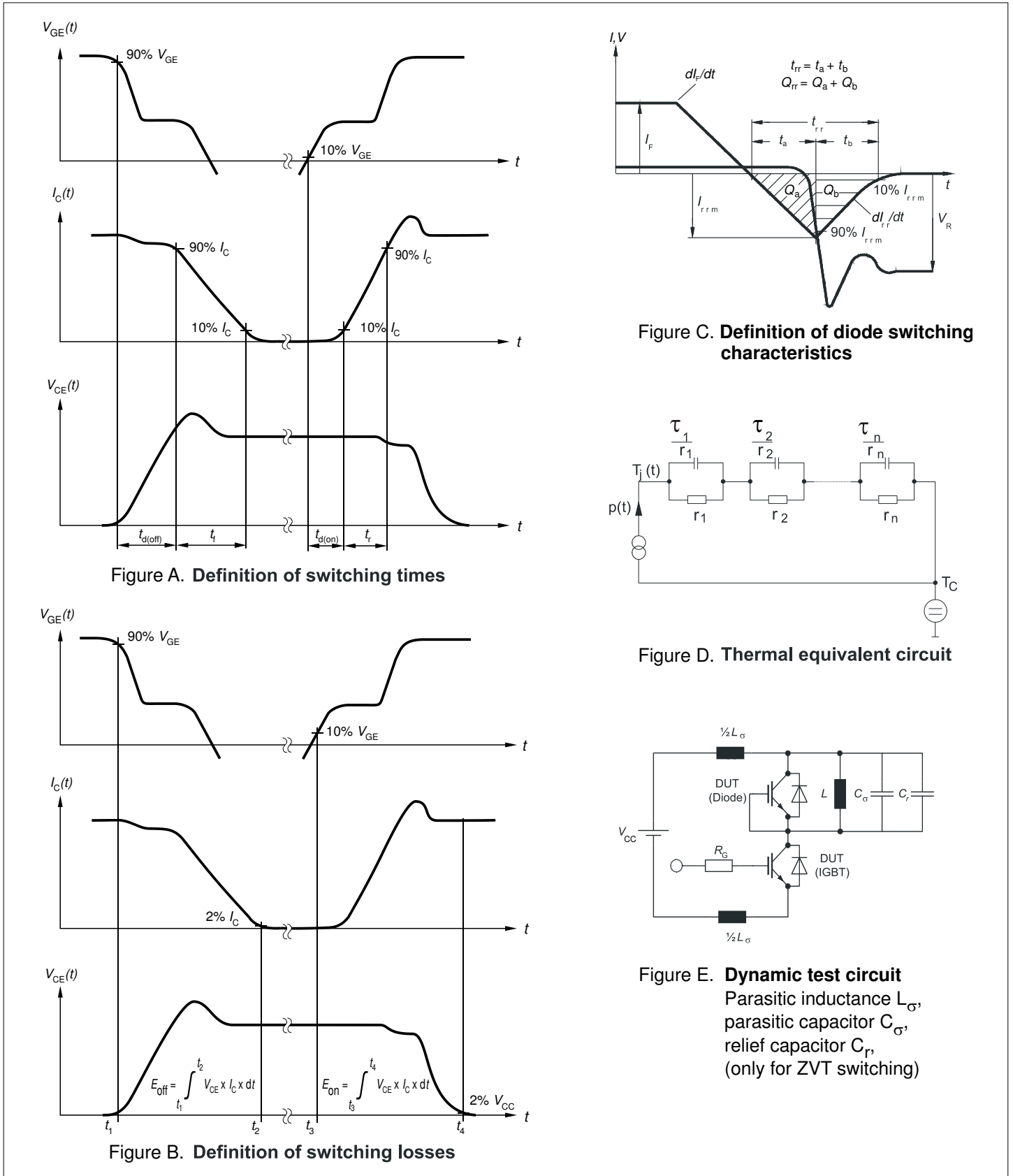


Figure 2

**Revision history**

<b>Document revision</b>	<b>Date of release</b>	<b>Description of changes</b>
1.00	2023-04-27	Final datasheet
1.10	2023-11-15	Update of energy diagrams



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